

Supplementary Materials

Effect of Long-Term Sodium Hypochlorite Cleaning on Silicon Carbide Ultrafiltration Membranes Prepared via Low-Pressure Chemical Vapor Deposition

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1. Thickness of SiC layer on silicon wafers at different deposition conditions measured by ellipsometry.

Table S1. SiC layer thickness as a function of different deposition conditions.

S.No.	Temperature (°C)	Pressure (mTorr)	Time (mins)	SiC Thickness (nm)
1.	750	600	60	16
2.	860	100	30	16

2. SiC-7-2A and SiC-8-2A membranes post-ageing.

SiC-7-2A



SiC-8-2A



Figure S1. SiC membranes after ageing in NaClO for 200hrs.